Supporting Information

Photodetection Tuning with High Absorptivity Using Stacked 2D Heterostructure Films

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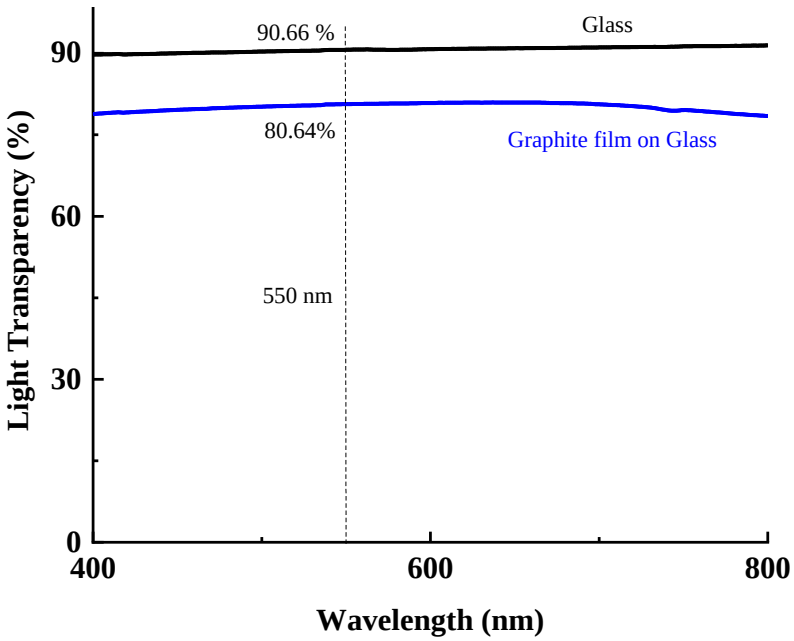

Figure S1. Light transparency of glass and intrinsic graphite film (15 nm thick)/glass.

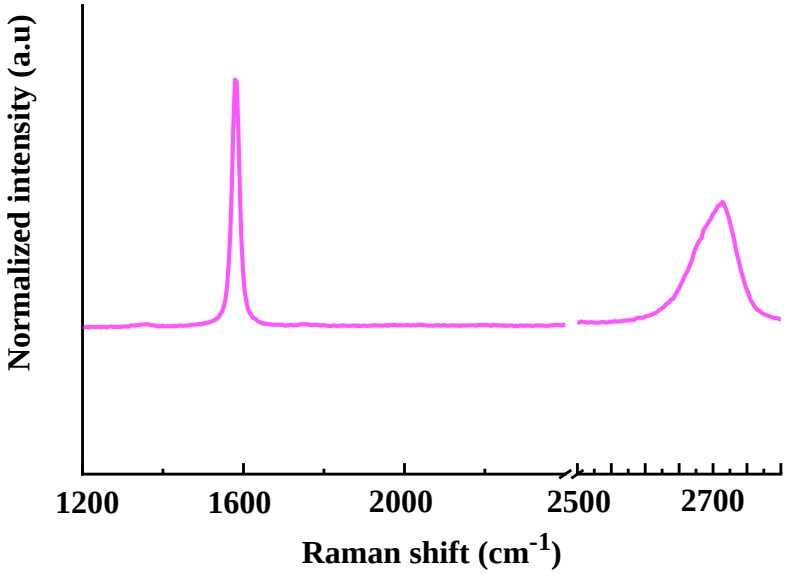

Figure S2. Raman spectra of intrinsic graphite film (15 nm thick).

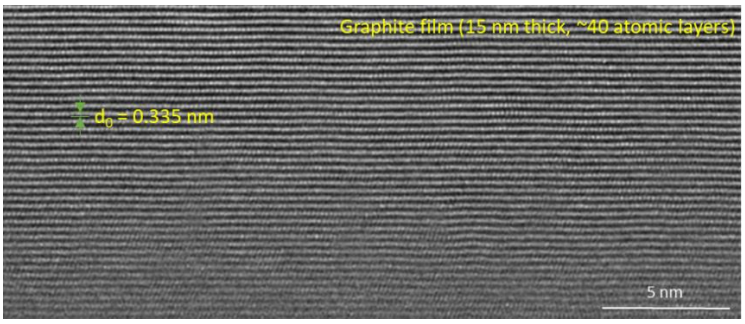

Figure S3. Cross-sectional TEM image of intrinsic graphite film (15 nm thick, >40 atomic layers).

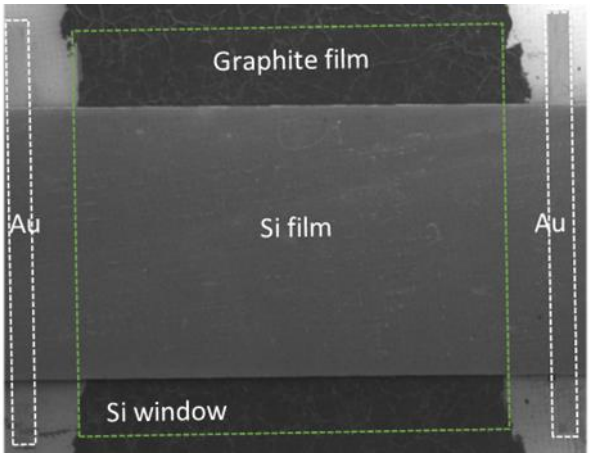

Figure S4. SEM image of Si film/graphite film/Si-stacked photodetection (PD) device.

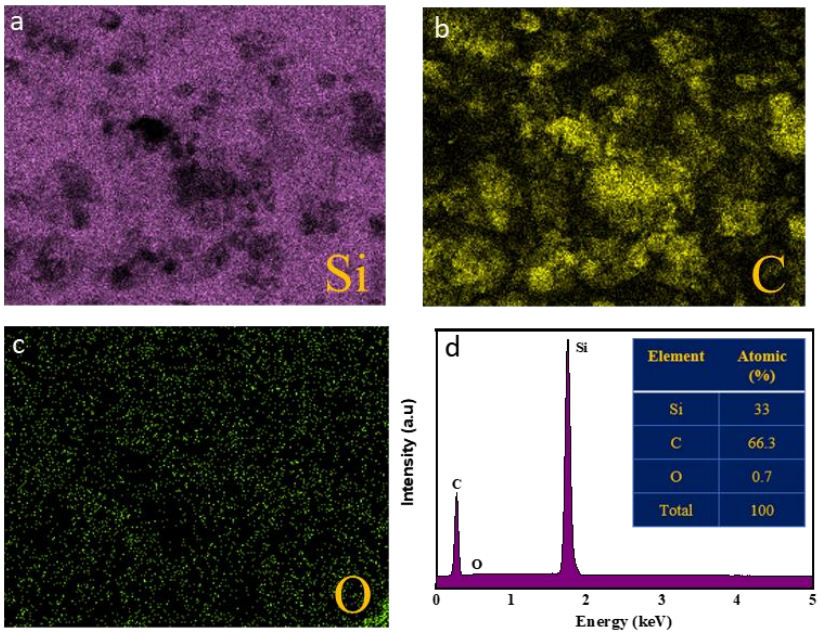

Figure S5. Energy dispersive X-ray spectroscopy (EDS) mapping and images of Si, O, and C elements of graphite film (15 nm thick) transferred on n-type Si substrate.

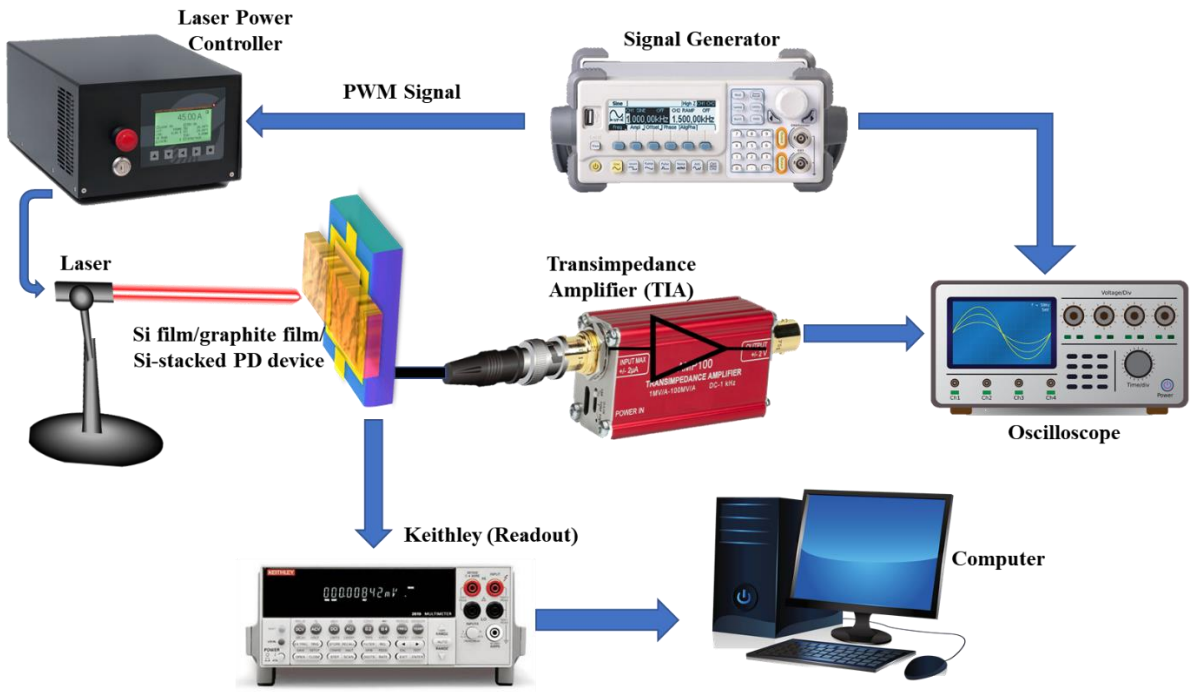

Figure S6. Schematic of the laser system setup for the measurement of characterizations in visible region of p-type Si film/graphite film/n-type Si-stacked Schottky photodiode.